

## Description

DW03C has built-in high-precision voltage detection circuit and delay circuit, which can realize overcharge, overdischarge and overcurrentprotection of the batterybydetecting the voltage and current of the battery. The protection circuit is suitablefor a single ithium ion/lithium polymerrechargeable battery.

## Features

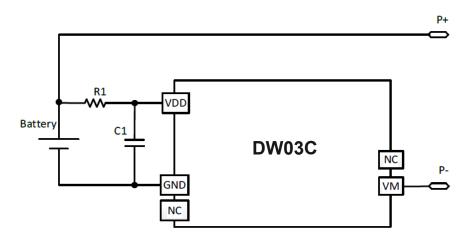
- High Precision Voltage Detection Function: 1. Overcharge Protection Voltage 4.300V Accuracy: ±25mV 4.100V 2. Overcharge Release Voltage Accuracy: ±50mV 3. Overdischarge Protection Voltage 2.400V Accuracy: ±100mV 3.000V 4. Overdischarge Release Voltage Accuracy: ±100mV 5. Discharge OverCurrent Detection 3.6A Accuracy: ±25% 6.Short Circuit Current Detection 12.0A Accuracy: ±30% 2.5A 7. Charging OverCurrent Detection Accuracy: ±25% Internal Detection Delay Time:: 1. Overcharge Protection Delay 1.0S Accuracy: ±50% 2. Overdischarge Protection Delay 64mS Accuracy: ±50% 3. Delay of Discharge Overcurrent 10mS Accuracy: ±50% 4.Delay of Charge Overcurrent 10mS Accuracy: ±50% Charger Detection and Load Detection Function Allow Function of Charging 0V Battery **Dormancy Function** No **Disconnect The Load** Conditions for Relieving Discharge Overcurrent The Release Voltage of Discharge Overcurrent State VRIOV Low Current Consumption 1. At Work 1.0µA(Typ.) (Ta=25°C) 0.5µA(Typ.) (Ta=25°C) 2. Overdischarge
- On-Resistance Ofinternal Power N-MOSFET: 60mΩ
- Lead-Free and Halogen-Free
- Operating Temperature Range: -40°C~+85°C
- Available Package: SOT-23-5

## Applications

• Protection IC for One-Cell Lithium-Ion /Lithium-Polymer Battery Pack



# **Typical Application Circuit**



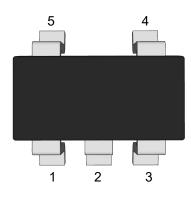
Device Identification	Min.	Min. Typ.		Unit
R1	510	1000	1500	Ω
C1	0.047	0.1	0.22	μF

Note :

1. The above parameters may be changed without notice.

2. The schematic diagram and parameters of IC are notused as the bass to ensure the circuit to work Please make filmeasurement on the actual application crcuit before seting the parameters.

# **Pin Distribution**



SOT-23-5

## **Functional Pin Description**

Pin NO.	Symbol	Pin Description
1,5	NC	Not Connected
2	GND	Ground Pin
3	VDD	Power Supply
4	VM	The charging and discharging current detection terminal is linked with the charger
4	VIVI	load or the load



# **Ordering Information**

Orderable Device	Package	Reel (inch)	Package Qty (PCS)	Eco Plan <sup>Note</sup>	MSL Level	Marking Code
DW03C	SOT-23-5	7	3000	RoHS & Green	MSL3	DW03

#### Note:

RoHS: PJ defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Green: PJ defines "Green" to mean Halogen-Free and Antimony-Free.

## **Product List**

#### 1.Detection Voltage Sheet

		Overcharge	Overcharge	Overdischarge	Overdischarge	Discharge	Short Circuit	Charging
Device	P	Protection	Release	Protection	Release	OverCurrent	Current	OverCurrent
Name	R <sub>DS(on)</sub>	Voltage	Voltage	Voltage	Voltage	Detection	Detection	Detection
		Voc	V <sub>OCR</sub>	V <sub>OD</sub>	V <sub>ODR</sub>	I <sub>DI</sub>	I <sub>SHORT</sub>	I <sub>CI</sub>
DW03C	33mΩ	4.300V	4.100V	2.400V	3.000V	3.6A	12A	2.5A

#### 2.Product Function Sheet

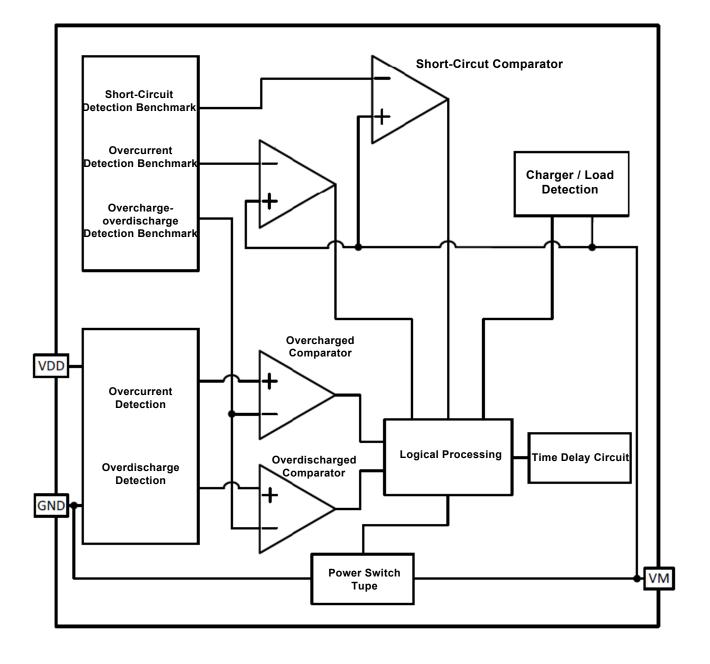
Devi Nan		Function of Charging 0V Battery	The Release Condition of Discharge Overcurrent State	The Release Voltage of Discharge Overcurrent State	Overcharge Self-recovery Function	Dormancy Function
DW0	)3C	Allow	断开负载	VRIOV	有	无

#### 3.Delay Time

Device Name	Overcharge Protection Delay T <sub>oc</sub>	Overdischarge Protection Delay T <sub>OD</sub>	Delay of Discharge Overcurrent T <sub>Di</sub>	Delay of Charge Overcurrent T <sub>Cl</sub>	Short Circuit Delay T <sub>SHORT</sub>
DW03C	1000ms	64ms	10ms	10ms	250µs



# **Block Diagram**





## Absolute Maximum Ratings Note

 $(T_A=25^{\circ}C, unless otherwise noted.)$ 

Parameter	Symbol	Rating	Unit
Input Voltage Between VDD and GND	VDD	-0.3 ~6	V
VM Pin Outtput Voltage	V <sub>VM</sub>	-6 ~10	V
Operating Ambient Temperature Range	T <sub>OPR</sub>	-40 ~ 85	°C
Storage Temperature Range	T <sub>STG</sub>	-55 ~ 125	°C
ESD(HBM State)	V <sub>ESD(HBM)</sub>	4000	V

Note :

The applied voltage exceeds the absolute maximum rating, which may cause irreversible damage to the chip.



# **Electrical Characteristics**

 $(T_A=25^{\circ}C$ , unless otherwise noted.)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Normal working current	I <sub>OPE</sub>	VDD=3.6V, V <sub>VM</sub> =0V	0.42	1.0	2.0	μA
Consume current during overdischarge	I <sub>OPED</sub>	VDD=2.0V,V <sub>VM</sub> floating		0.5	1.0	μA
Overcharge Protection Voltage	Voc	VDD=3.5→4.8V	4.275	4.300	4.325	V
Overcharge Release Voltage	V <sub>OCR</sub>	VDD=4.8→3.5V	4.050	4.100	4.150	V
Overdischarge Protection Voltage	Vod	VDD=3.5→2.0V	2.300	2.400	2.500	V
Overdischarge Release Voltage	V <sub>ODR</sub>	VDD=2.0→3.5V	2.900	3.000	3.100	V
Discharge Overcurrent Release Voltage	Vriov		VDD-1.2	VDD-0.8	VDD-0.5	V
Discharge OverCurrent Detection	I <sub>DI</sub>	VDD=3.6V	2.7	3.6	4.5	A
Short Circuit Current Detection	Ishort	VDD=3.6V	8.4	12	15.6	A
Charging OverCurrent Detection	I <sub>CI</sub>	VDD=3.6V	1.87	2.5	3.13	A
Overcharge Protection Delay	Toc	VDD=3.5→4.8V	500	1000	1500	ms
Overdischarge Protection Delay	T <sub>OD</sub>	VDD=3.5→2.0V	32	64	96	ms
Delay of Discharge Overcurrent	T <sub>DI</sub>	VDD=3.6V	5	10	15	ms
Delay of Charge Overcurrent	T <sub>CI</sub>	VDD=3.6V	5	10	15	ms
Short Circuit Delay	T <sub>SHORT</sub>	VDD=3.6V	100	250	400	μs
Resistance Between VDD and VM	R <sub>CMD</sub>	VDD=2V, V <sub>VM</sub> =0V	750	1500	3000	kΩ
Resistance Between VDD and GND	R <sub>VMS</sub>	VDD=3.6V, V <sub>VM</sub> =1.0V	10	20	30	kΩ
On-Resistance Ofinternal Power N-MOSFET	R <sub>SS(ON)</sub>	VDD=3.6V, I <sub>VM</sub> =0.1A		60		mΩ
0V Charging, Charger Starting Voltage	V <sub>0CH</sub>	Allow charging to 0V battery	0.0	1.5	2.0	V



# **Electrical Characteristics**

 $(T_A=20^{\circ}C\sim60^{\circ}C$ , unless otherwise noted.)

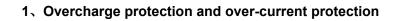
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Normal working current	I <sub>OPE</sub>	VDD=3.6V, V <sub>VM</sub> =0V	0.42	1.0	2.0	μA
Consume current during overdischarge	I <sub>OPED</sub>	VDD=2.0V,V <sub>VM</sub> floating		0.5	1.0	μA
Overcharge Protection Voltage	Voc	VDD=3.5→4.8V	4.250	4.300	4.350	V
Overcharge Release Voltage	V <sub>OCR</sub>	VDD=4.8→3.5V	4.000	4.100	4.200	V
Overdischarge Protection Voltage	V <sub>OD</sub>	VDD=3.5→2.0V	2.200	2.400	2.600	V
Overdischarge Release Voltage	V <sub>ODR</sub>	VDD=2.0→3.5V	2.800	3.000	3.200	V
Discharge Overcurrent Release Voltage	V <sub>RIOV</sub>		VDD-1.3	VDD-0.8	VDD-0.4	V
Discharge OverCurrent Detection	I <sub>DI</sub>	VDD=3.6V	1.8	3.6	5.4	А
Charging OverCurrent Detection	Icı	VDD=3.6V	1.25	2.5	3.75	A
Overcharge Protection Delay	T <sub>oc</sub>	VDD=3.5→4.8V	300	1000	1700	ms
Overdischarge Protection Delay	Тор	VDD=3.5→2.0V	19.2	64	108.8	ms
Delay of Discharge Overcurrent	T <sub>DI</sub>	VDD=3.6V	3	10	17	ms
Delay of Charge Overcurrent	T <sub>CI</sub>	VDD=3.6V	3	10	17	ms
Short Circuit Delay	T <sub>SHORT</sub>	VDD=3.6V	75	250	500	μs
Resistance Between VDD and VM	R <sub>CMD</sub>	VDD=2V, V <sub>VM</sub> =0V	500	1500	6000	kΩ
Resistance Between VDD and GND	R <sub>VMS</sub>	VDD=3.6V, V <sub>VM</sub> =1.0V	7	20	40	kΩ
On-Resistance Ofinternal Power N-MOSFET	R <sub>SS(ON)</sub>	VDD=3.6V, I <sub>VM</sub> =0.1A		60		mΩ
0V Charging, Charger Starting Voltage	V <sub>0CH</sub>	Allow charging to 0V battery	0.0	1.5	2.5	V

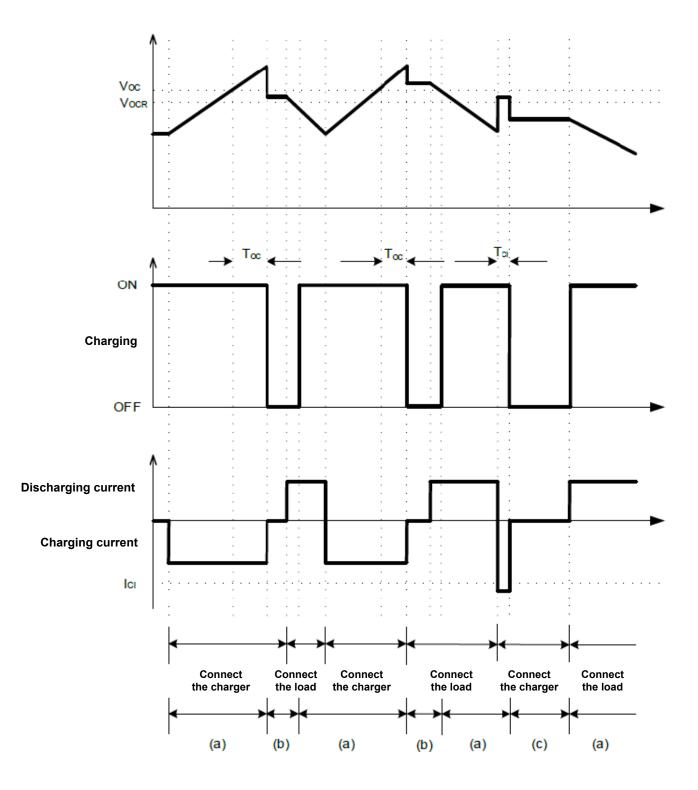
Note :

The scieenine is not caried out under the conditions of hig temperature and low temperature, so only the initial votape of the esign specs in this temperature rane is guaranteed



# Sequence Chart



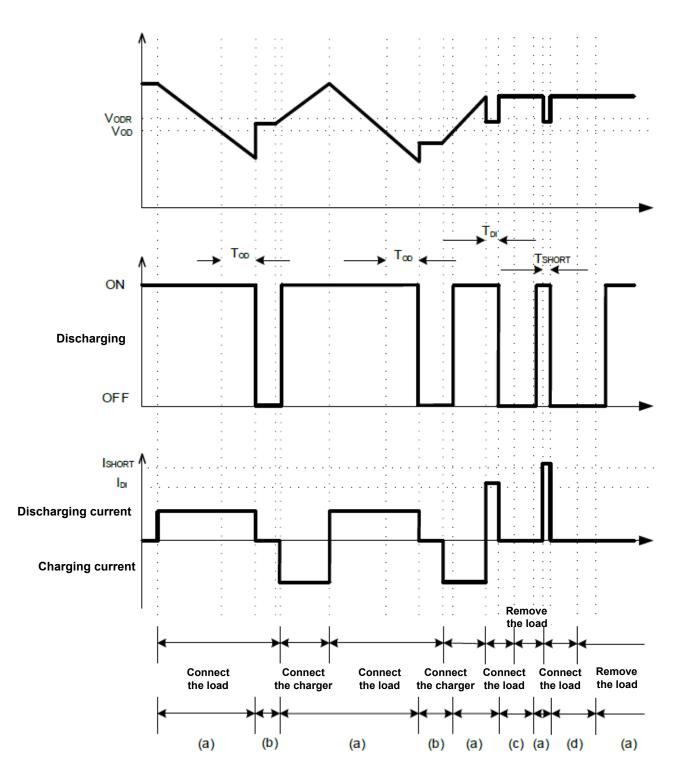


<sup>(</sup>a) Normal operating state

- (b) Overcharged state
- (c) charging overcurrent state



## 2. Overdischarge protection and discharge overcurrent protection



- (a) Normal working state
- (b) Overdischarge state
- (c) Discharge overcurrent state
- (d) load short-circuit state



## **Function Description**

#### 1. Normal Operating State

This IC continuously detects the battery voltage connected between the VDD and GND terminals, as well as the current flowing between the VM and GND terminals, to control charge and discharge. When the battery voltage is above the overdischarge protection voltage ( $V_{OD}$ ) and below the overcharge protection voltage ( $V_{OC}$ ), and the current flowing through the VM terminal to GND is between the charge overcurrent protection threshold ( $I_{CI}$ ) and discharge overcurrent protection threshold ( $I_{DI}$ ), the internal MOSFET of the IC is switched on. This state is called "normal working state". In this state, the MOSFET can be charged and discharged normally.

#### 2. Overcharge State

When during the charging process under normal conditions, when the battery voltage is higher than the overcharge detection voltage ( $V_{OC}$ ), and the duration reaches the overcharge voltage detection delay time ( $T_{OC}$ ) or longer, the internal MOSFETof IC will turn off and stop charging, this situation is called overcharge voltage protection. The overcharge state can be lifted under the following two conditions:

(1). VM<V<sub>LD</sub>, when the battery voltage is lowered below the overcharge release voltage ( $V_{OCR}$ ), the overcharge state will be released.

(2). VM>V<sub>LD</sub>, when the battery voltage is reduced to the overcharge protection voltage ( $V_{OC}$ ) below, the overcharge state is lifted and returned to the normal working state, this function is called the load detection function.

Here  $(V_{LD}) = I_{DI} * R_{SS(ON)}$ , is the load detection voltage set inside the IC.

#### 3. Overdischarge State

After the battery voltage drops below  $V_{OD}$  and the well continues  $T_{OD}$  for a period of time, the internal MOSFET of IC will turn off and stop discharging, which is called the overdischarge state. When the MOSFET inside the IC is turned off, the VM will be pulled up to VDD by the internal pull-up resistor  $R_{VMD}$ , and the IC power consumption will be reduced to  $I_{OPED}$ .

After entering the overdischarge state, to remove the overdischarge state and return to the normal state, there are several situations:

(1) Connect the charger, if VM<0V(typical value), when the battery voltage is higher than the overdischarge protection voltage (VOD), the overdischarge state is lifted and restored to the normal working state, this function is called the charger detection function.

(2) Connect the charger, if VM>0V(typical value), when the battery voltage is higher than the overdischarge release voltage ( $V_{ODR}$ ), the overdischarge state is lifted and restored to the normal working state.

(3) When the charger is not connected, when the battery voltage is higher than the overdischarge release voltage (V<sub>ODR</sub>), the overdischarge state is released and returned to the normal working state, that is, "no sleep function".

#### 4. Discharge Overcurrent State

In the normal working state of the battery, the IC continuously detects the discharge current through the VM terminal voltage. If the discharge current exceeds the discharge current Limiting value ( $I_{DI}$ ), and this state lasts longer than the discharge overcurrent Protection Delay time ( $T_{DI}$ ), the internal MOSFETof IC will turn off and stop discharging. This state is called the discharge overcurrent state. If the discharge current exceeds the short-circuit protection current value, and this state lasts longer than the load short-circuit protection delay time ( $T_{SHORT}$ ), the MOSFET inside the IC will turn off and stop discharging. This state is called the "load short-circuit state.

Discharge overcurrent state release condition "disconnect load" and discharge overcurrent state release voltage "V<sub>RIOV</sub>"

In the discharge overcurrent state, the VM terminal inside the chip and the GND terminal can be connected through the  $R_{VMS}$  resistor. However, during the connection to the load, the VM terminal voltage changes to the VDD terminal voltage due to the connection to the load. If the connection to the load is disconnected, the VM terminal reverts to the GND terminal voltage. When the VM terminal voltage drops below  $V_{RIOV}$ , the discharge overcurrent state can be lifted.



#### 5. Charge Overcurrent Protection

For a battery in normal working condition, if the current value flowing through GND to VM exceeds the charge overcurrent protection value ( $I_{CI}$ ) during charging, and the state lasts longer than the charge overcurrent protection Delay time ( $T_{CI}$ ), the internal MOSFET IC will turn off and stop charging. This state is called charging overcurrent state. After entering the state of charge overcurrent detection, if disconnect the charger to make the flow through GND to When the current of the VM terminal is lower than the overcurrent protection value ( $I_{CI}$ ), the charging overcurrent state is removed and returned to the normal working state.

#### 6. Charging Function to 0V Battery(Allowed)

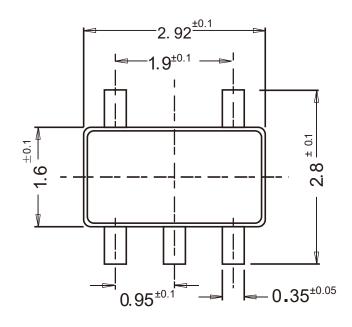
This function is used to recharge the battery that has self-discharged to 0V. When the charger voltage connected between the positive battery (P+) and the negative battery (P-) is higher than the charger starting voltage ( $V_{0CH}$ ) to charge the 0V battery, the IC internal charge control MOSFET will switch on and start charging. When the battery voltage is higher than the overdischarge protection voltage ( $V_{0D}$ ), the IC enters the normal working state.

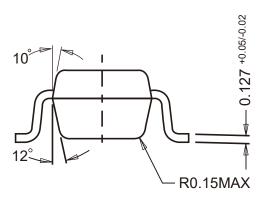
Note: Please ask the battery supplier to confirm whether the purchased battery has the "allow charging to the 0V battery" function or the "do not charge to the 0V battery" function".

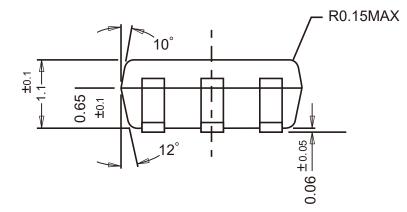


# Package Outline

# SOT-23-5 Dimensions in mm



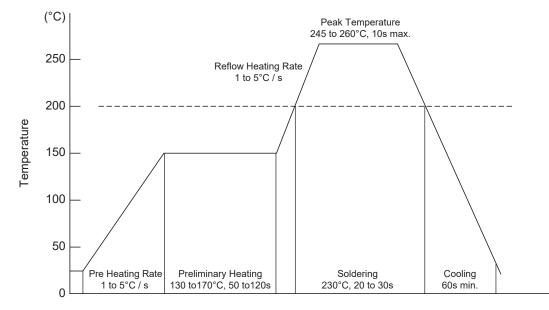






# **Conditions of Soldering and Storage**

## Recommended condition of reflow soldering



Recommended peak temperature is over 245°C. If peak temperature is below 245°C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)
- Conditions of hand soldering
- Temperature: 300°C
- Time: 3s max.
- Times: one time

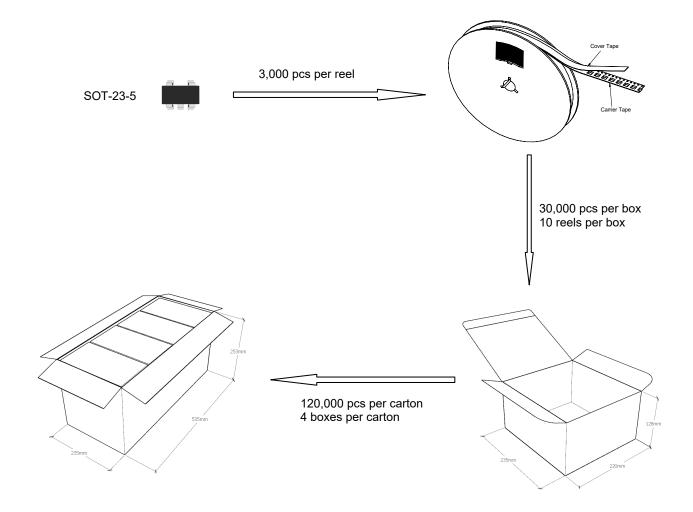
#### • Storage conditions

- Temperature
  - 5 to 40°C
- Humidity
  30 to 80% RH
- Recommended period One year after manufacturing



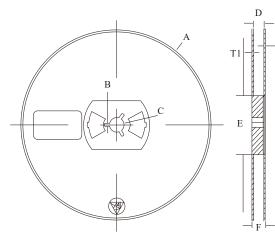
# **Package Specifications**

• The method of packaging



Т2

#### reel data





Symbol	Value (unit: mm)
A	Ø 177.8±1
В	2.7±0.2
С	Ø 13.5±0.2
E	Ø 54.5±0.2
F	12.3±0.3
D	9.6+2/-0.3
T1	1.0±0.2
T2	1.2±0.2



Embossed tape data

